



TENSOR D-RINSE

ADDITIVE FOR HIGH PRESSURE PAD RINSE/WAFER DE-CHUCKING CYCLES

Tensor D-Rinse is a specially formulated additive designed for use in high-pressure pad rinse and wafer de-chucking systems of today's CMP tools.

When added to the rinse water at concentrations between 10% and 25% Tensor D-Rinse will reduce light scratching produced during the high-pressure rinse/de-chucking cycle. Tensor D-Rinse will also facilitate removal of slurry chemistry, particles and pad residues, thus increasing the effectiveness of post-CMP (megasonic and brush) wafer cleaning processes. Tensor D-Rinse is formulated to eliminate corrosion/oxidation of metals that can occur during wafer transport to 2nd and 3rd phases as well as delayed transport to the cleaning station.

Benefits:

- Superior wetting with low foam
- Free rinsing – leaves no films or residue
- Cleans residues left by any commercially available CMP slurries
- Fully compatible with advanced metal schemes and associated dielectrics
- Fully compatible with all industry standard CMP tools and pad rinsing/wafer dechucking systems
- Easily implemented
- Safe and economical to use

Directions:

It is recommended that Tensor D-Rinse be added to the high-pressure water rinse line at 10% to 25%. The types of post-CMP residues, length of time under the spray, spray pressure, slurry chemistry and other process factors ultimately determine specific dilutions and methods of use.

Additional Information:

Intersurface Dynamics manufactures 3 product lines, TENSOR, VECTOR and CHALLENGE Series Products. Visit our web site at www.isurface.com for more information.